IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Kelly T. Hurley

Serial No.: Unknown

Filed: Concurrently herewith

For:

FLASH FLOATING GATE USING

EPITAXIAL GROWTH

Group Art Unit: Unknown

Examiner: Unknown

Atty. Docket: 2000-0133.00

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

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Signature

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant respectfully requests that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. Copies of the listed references are enclosed for the convenience of the Examiner.

In accordance with 37 C.F.R. § 1.97(b), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following references are submitted for the Examiner's review:

U.S. Patents

U.S. Patent No. Issue Date Inventor
5,210,047 May 11, 1993 Woo et al.

Articles

"Novel 0.44µm² Ti-Salicide STI Cell Technology for High Density NOR Flash Memories and High Performance Embedded Application", H. Watanabe et al., IEDM 98, pp. 975-978

"A 130-mm², 256-Mbit NAND Flash with Shallow Trench Isolation Technology", Kenichi Imamiya et al., IEEE Journal of Solid-State Circuits, Vol. 34, No. 11, November 1999

As this information is being submitted within three months of the date of filing of the application, Applicant understands that no fee or certification is required for the submission and consideration of this information at this time.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicant's undersigned attorney at the number indicated.

* * * *

A Form PTO-1449 is enclosed herewith.

Respectfully submitted,

Date: 7/13/2001 David J. Paul

Reg. No. 34,692

Micron Technology, Inc. 8000 S. Federal Way Boise, ID 83706-9632

(208) 368-4515

AGENT FOR APPLICANT

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Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation EXAMINER: if not in conformance and not considered. Include copy of this form with next communication with applicant.